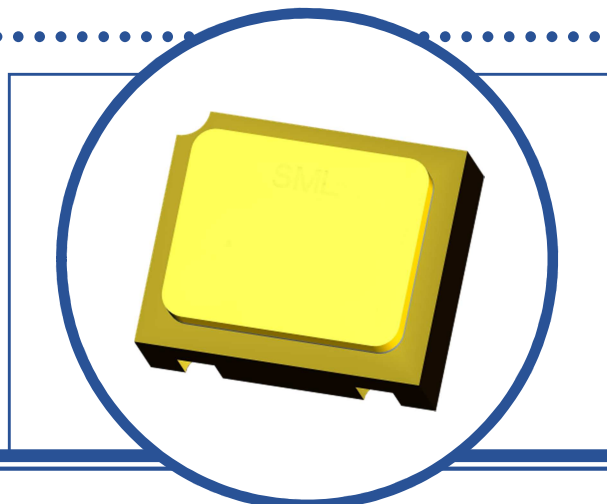


SILICON SMALL SIGNAL N-CHANNEL JFET

2N4392CSM

- Hermetic Surface Mounted Package
- Designed For High Reliability and Space Applications
- Screening Options Available



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise stated)

V _{DS}	Drain – Source Voltage	40V
V _{GS}	Gate – Source Voltage	-40V
V _{GD}	Gate – Drain Voltage	-40V
I _G	Gate Current	50mA
P _D	Total Power Dissipation at T _A = 25°C De-rate Above 25°C	300mW 2mW/°C
T _J	Junction Temperature Range	-55 to +175°C
T _{stg}	Storage Temperature Range	-65 to +200°C

THERMAL PROPERTIES

Symbols	Parameters	Max.	Units
R _{θJA}	Thermal Resistance, Junction To Ambient	500	°C/W

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



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SILICON SMALL SIGNAL N-CHANNEL JFET 2N4392CSM

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)GSS}$	Gate – Source Breakdown Voltage	$V_{DS} = 0V$ $I_G = 1.0\mu A$	-40			V
$V_{GS(off)}$	Gate – Source Cut-off Voltage	$V_{DS} = 20V$ $I_D = 1.0nA$	-2		-5	
$I_{DSS}^{(1)}$	Saturation Drain Current	$V_{DS} = 20V$ $V_{GS} = 0V$	25		75	mA
I_{GSS}	Gate Reverse Current	$V_{DS} = 0V$ $V_{GS} = -20V$			-100	pA
			$T_A = 150^\circ\text{C}$			-200
$I_{D(off)}$	Drain Cut-off Current	$V_{DS} = 20V$ $V_{GS} = -7V$			100	pA
			$T_A = 150^\circ\text{C}$			200
$V_{DS(on)}$	Drain – Source On Voltage	$V_{GS} = 0V$ $I_D = 6mA$			0.4	V
$R_{DS(on)}$	Drain – Source On Resistance	$V_{GS} = 0$ $I_D = 1.0mA$			60	Ω

DYNAMIC CHARACTERISTICS

C_{iss}	Common – Source Input Capacitance	$V_{DS} = 20V$ $f = 1.0MHz$	$V_{GS} = 0V$			26	pF
C_{rss}	Common – Source Reverse Transfer Capacitance	$V_{DS} = 0V$ $f = 1.0MHz$	$V_{GS} = -7V$			5	
$R_{DS(on)}$	Drain – Source On Resistance	$V_{GS} = 0$ $f = 1.0KHz$	$I_D = 0A$			60	Ω
t_r	Rise Time	$V_{DD} = 10V$ $V_{GS} = 0V$	$V_{GSX} = -7V$ $I_{D(on)} = 6mA$			5	ns
$t_{d(on)}$	Turn-on Delay Time					15	
t_f	Fall Time					20	
$t_{d(off)}$	Turn-off Delay Time					35	

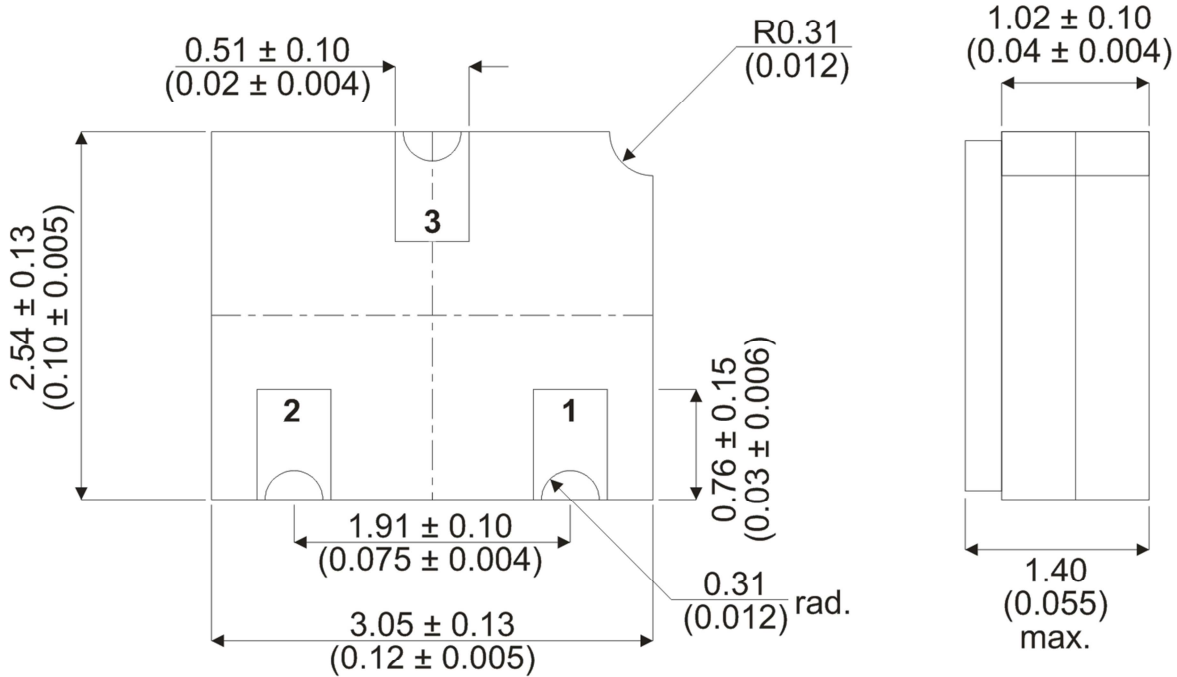
Notes

(1) Pulse Width $\leq 380\mu s$, $\delta \leq 2\%$

SILICON SMALL SIGNAL N-CHANNEL JFET 2N4392CSM

MECHANICAL DATA

Dimensions in mm (inches)



**LCC1 (SOT23)
Underside View**

Pad 1	Pad 2	Pad 3
Source	Drain	Gate